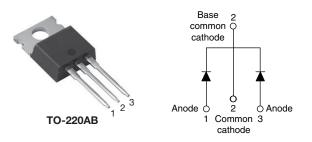
**Vishay Semiconductors** 

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High Performance Schottky Rectifier, 2 x 15 A



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 x 15 A				
V <sub>R</sub>	100 V				
V <sub>F</sub> at I <sub>F</sub>	0.67 V				
I <sub>RM</sub> max.	7.0 mA at 125 °C				
T <sub>J</sub> max.	175 °C				
E <sub>AS</sub>	7.50 mJ				
Package	TO-220AB				
Circuit configuration	Common cathode				

### FEATURES

- 175 °C T<sub>J</sub> operation
- Low forward voltage drop
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance



- Guard ring for enhanced ruggedness and long term reliability
- AEC-Q101 qualified, meets JESD 201, class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### DESCRIPTION

The center tap Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS VALUES					
I <sub>F(AV)</sub>	Rectangular waveform	30	А			
V <sub>RRM</sub>		100	V			
I <sub>FSM</sub>	t <sub>p</sub> = 5 μs sine	850	А			
V <sub>F</sub>	15 A <sub>pk</sub> , T <sub>J</sub> = 125 °C (per leg)	0.67	V			
TJ	Range	-55 to +175	°C			

VOLTAGE RATINGS							
PARAMETER	SYMBOL	VS-30CTQ100HN3	UNITS				
Maximum DC reverse voltage	V <sub>R</sub>	100	V				
Maximum working peak reverse voltage	V <sub>RWM</sub>	100	v				

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST COND	ITIONS	VALUES	UNITS			
Maximum average forward per device	I	50 % duty cycle at $T_{C}$ = 129 °C, rectangular waveform		30	А			
current, see fig. 5 per leg	I <sub>F(AV)</sub>			15	A			
Maximum peak one cycle non-repetitive	<b>I</b> ==++	5 $\mu s$ sine or 3 $\mu s$ rect. pulse	Following any rated load condition and with rated	850	A			
surge current per leg, see fig. 7	I <sub>FSM</sub>	10 ms sine or 6 ms rect. pulse	$V_{\text{RRM}}$ applied	275				
Non-repetitive avalanche energy per leg	E <sub>AS</sub>	$T_J = 25 \text{ °C}, I_{AS} = 0.50 \text{ A}, L = 60 \text{ mH}$		7.50	mJ			
Repetitive avalanche current per leg		Current decaying linearly to zero in 1 $\mu$ s Frequency limited by T <sub>J</sub> maximum V <sub>A</sub> = 1.5 x V <sub>R</sub> typical		0.50	А			

Revision: 31-Oct-2019

Document Number: 96670

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PARAMETER	SYMBOL	TEST CO	VALUES	UNITS		
		15 A	T <sub>.1</sub> = 25 °C	0.86		
Maximum forward voltage drop per leg See fig. 1	V (1)	30 A	$1_{\rm J} = 25$ C	1.05	V	
	V <sub>FM</sub> <sup>(1)</sup>	15 A	T 105 00	0.67		
		30 A	T <sub>J</sub> = 125 °C	0.82		
Maximum reverse leakage current per leg	I <sub>RM</sub> <sup>(1)</sup>	T <sub>J</sub> = 25 °C	$V_{\rm B}$ = Rated $V_{\rm B}$	0.55	<b>m</b> A	
See fig. 2	IRM (*)	T <sub>J</sub> = 125 °C	$v_{\rm R} = naleu v_{\rm R}$	7.0	mA	
Maximum junction capacitance per leg	CT	$V_R = 5 V_{DC}$ (test signal range	500	pF		
Typical series inductance per leg	L <sub>S</sub>	Measured lead to lead 5 m	8.0	nH		
Maximum voltage rate of change	dV/dt	Rated V <sub>R</sub>	10 000	V/µs		

#### Note

Γ

 $^{(1)}\,$  Pulse width < 300  $\mu s,$  duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			
Maximum thermal resistance, junction to case per leg				3.25				
Maximum thermal resistance, junction to case per package		- R <sub>thJC</sub>	DC operation	1.63	°C/W			
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.50				
Approximate weight				2	g			
Approximate weight				0.07	oz.			
Manuatian tanan	minimum			6 (5)	kgf ⋅ cm			
Mounting torque –	maximum			12 (10)	(lbf ⋅ in)			
Marking device			Case style TO-220AB	30CTC	Q100H			



# **VS-30CTQ100HN3**

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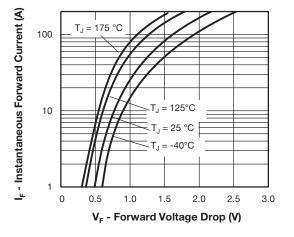


Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)

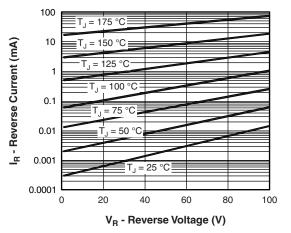


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage (Per Leg)

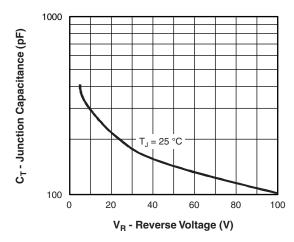


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

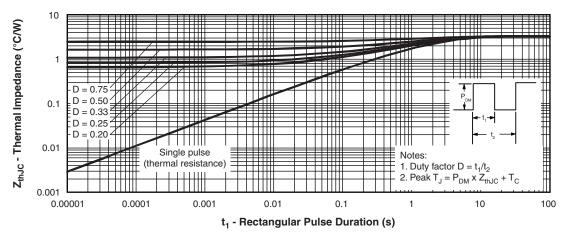
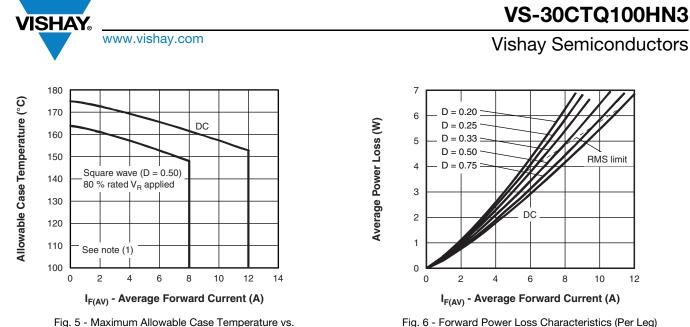
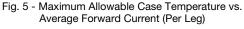
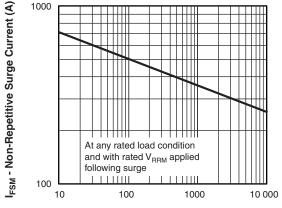


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Leg)

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t<sub>p</sub> - Square Wave Pulse Duration (μs)

Fig. 7 - Maximum Non-Repetitive Surge Current (Per Leg)

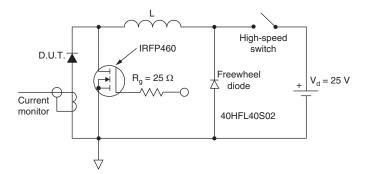


Fig. 8 - Unclamped Inductive Test Circuit

#### Note

- Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ; (1)
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})} / \mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{10} \ \mathsf{V} \end{array}$

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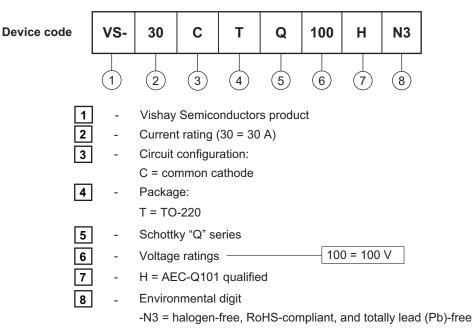
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ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-30CTQ100HN3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95222				
Part marking information	www.vishay.com/doc?95028				

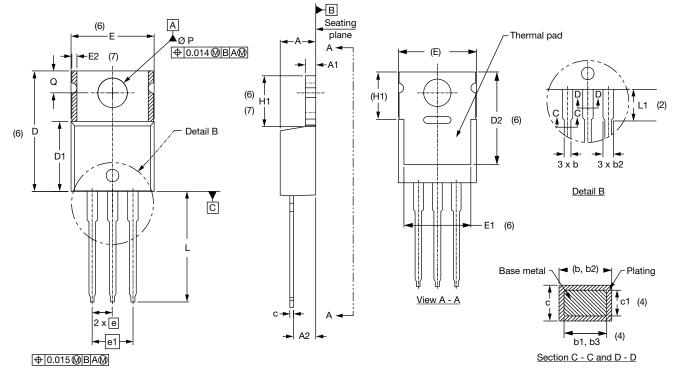
# **Outline Dimensions**



**Vishay Semiconductors** 

**TO-220AB** 

### **DIMENSIONS** in millimeters and inches



Lead tip

reten Teten reten

Conforms to JEDEC<sup>®</sup> outline TO-220AB

SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES SYN	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.56	2.92	0.101	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			E2	-	0.76	-	0.030	7
b1	0.38	0.97	0.015	0.038	4		е	2.41	2.67	0.095	0.105	
b2	1.20	1.73	0.047	0.068			e1	4.88	5.28	0.192	0.208	
b3	1.14	1.73	0.045	0.068	4		H1	5.84	6.86	0.230	0.270	6, 7
С	0.36	0.61	0.014	0.024			L	13.52	14.02	0.532	0.552	
c1	0.36	0.56	0.014	0.022	4		L1	3.32	3.82	0.131	0.150	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Dimension b1, b3 and c1 apply to base metal only

<sup>(5)</sup> Controlling dimensions: inches

<sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1

- <sup>(7)</sup> Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC<sup>®</sup> TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Revision: 23-Feb-2024	1	Document Number: 95222
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Revision: 01-Jan-2024